

ABSTRACT

METHOD AND APPARATUS FOR A FLASH MEMORY DEVICE COMPRISING A SOURCE LOCAL INTERCONNECT

A method for forming a flash memory device having a local interconnect connecting source regions of a plurality of transistors within a sector allows for a highly-selective wet etch of a dielectric region overlying the source region. An embodiment of the method comprises the use of an etch-resistant layer covering various features such as any gate oxide remaining over the source region, spacers along sidewalls of the transistor stacks, and a capping layer of the transistor. An in-process semiconductor device resulting from the inventive method is also disclosed.